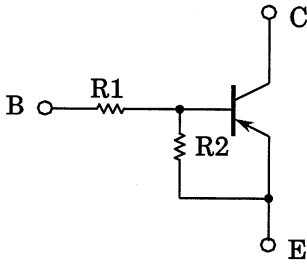
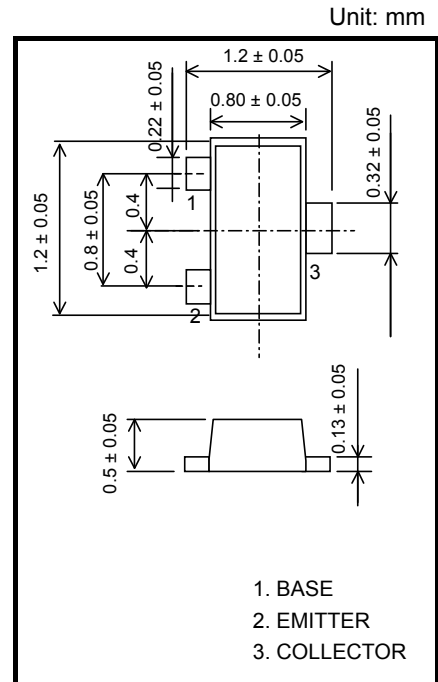


Silicon PNP Epitaxial Type (PCT Process)

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
3906	2.2	47

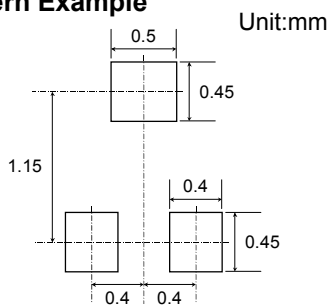


Weight: 1.5 mg

Absolute Maximum Ratings (Ta = 25°C)

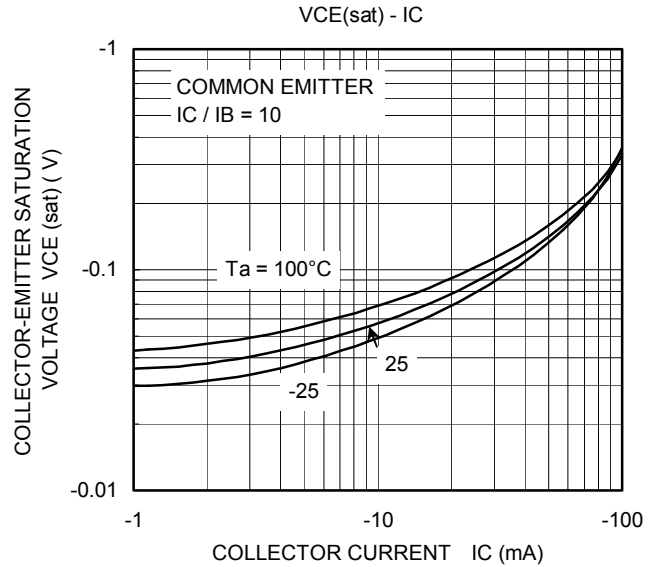
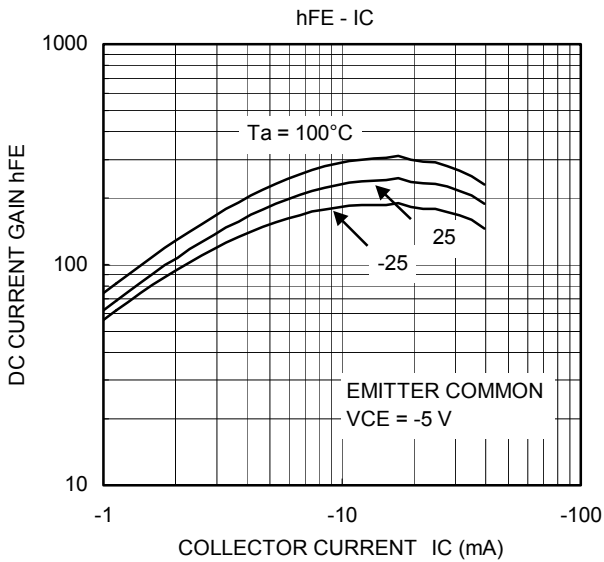
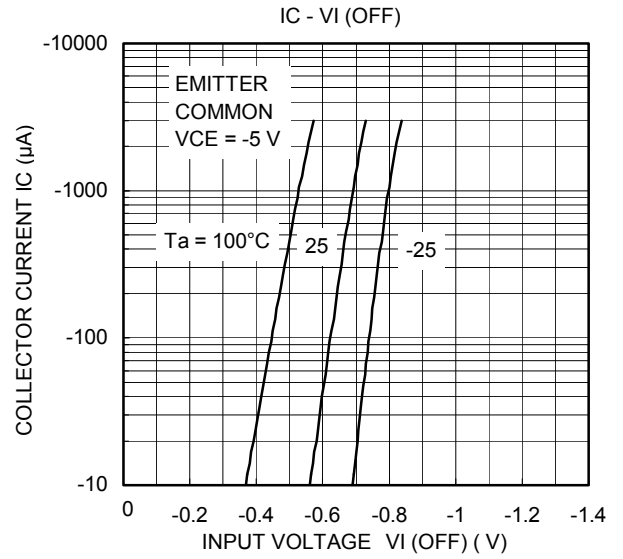
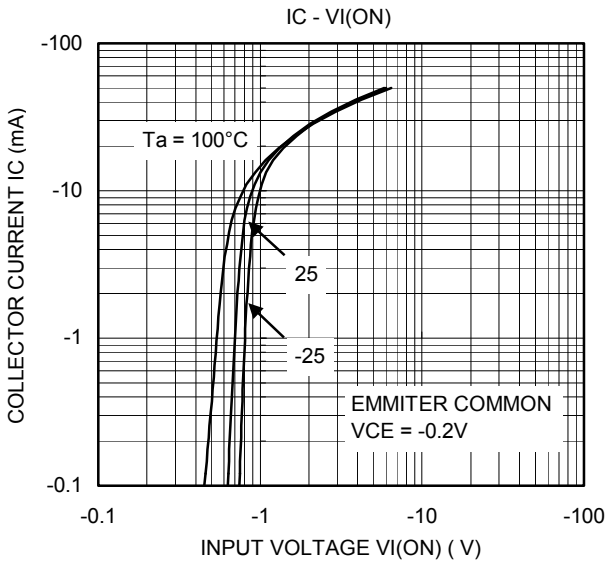
Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-10	V
		-5	
Collector current	I_C	-100	mA
Collector power dissipation	P_C (Note 1)	150	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to 150	°C

Land Pattern Example



Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	I _{CB0}	—	V _{CB} = -50 V, I _E = 0	—	—	-100	nA
	I _{CEO}		V _{CE} = -50 V, I _B = 0	—	—	-500	
Emitter cutoff current	I _{EBO}	—	V _{EB} = -5 V, I _C = 0	-0.078	—	-0.145	mA
DC current gain	h _{FE}	—	V _{CE} = -5 V, I _C = -10 mA	80	—	—	—
Collector-emitter saturation voltage	V _{CE (sat)}	—	I _C = -5 mA, I _B = -0.5 mA	—	-0.1	-0.3	V
Input voltage (ON)	V _{I (ON)}	—	V _{CE} = -0.2 V, I _C = -5 mA	-0.6	—	-1.1	V
Input voltage (OFF)	V _{I (OFF)}	—	V _{CE} = -5 V, I _C = -0.1 mA	-0.5	—	-0.8	V
Transition frequency	f _T	—	V _{CE} = -10V, I _C = -5mA	—	250	—	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = -10 V, I _E = 0, f = 1 MHz	—	0.9	—	pF



Type Name	Marking
3906	<p>Type Name</p>